

Yukihiro Harada

List of Publications by Year in Descending Order

Source: <https://exaly.com/author-pdf/9471934/yukihiro-harada-publications-by-year.pdf>

Version: 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

49
papers

466
citations

14
h-index

20
g-index

64
ext. papers

532
ext. citations

2.6
avg, IF

3.57
L-index

#	Paper	IF	Citations
49	Yb-doped YAlO ₃ thin films with a self-organized columnar structure and their anti-Stokes photoluminescence properties. <i>AIP Advances</i> , 2022 , 12, 025110	1.5	
48	Properties of Anti-Stokes Photoluminescence and Ideal Laser Cooling Performance in Yb-Doped Yttrium Aluminum Garnet Thin Film. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2020 , 69, 727-732	0.1	1
47	An energy transfer accompanied by phonon absorption in ytterbium-doped yttrium aluminum perovskite for optical refrigeration. <i>Applied Physics Letters</i> , 2020 , 117, 041104	3.4	2
46	Bandwidth enhancement in an InGaN/GaN three-section superluminescent diode for optical coherence tomography. <i>Applied Physics Letters</i> , 2020 , 117, 061106	3.4	2
45	Actual Calculation of Solar Cell Efficiencies. <i>Green Energy and Technology</i> , 2019 , 81-137	0.6	
44	Hot-carrier generation and extraction in InAs/GaAs quantum dot superlattice solar cells. <i>Semiconductor Science and Technology</i> , 2019 , 34, 094003	1.8	7
43	Energy Conversion Efficiency of Solar Cells. <i>Green Energy and Technology</i> , 2019 ,	0.6	5
42	Ideal Laser Cooling Efficiency Utilizing Anti-Stokes Luminescence in Yb-Doped Yttrium Aluminum Garnet Powder Crystals. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2019 , 68, 762-766	0.1	
41	Improving laser cooling efficiencies of Yb-doped yttrium aluminum garnet by utilizing non-resonant anti-Stokes emission at high temperatures. <i>Optics Express</i> , 2019 , 27, 34961-34973	3.3	5
40	Bound-to-continuum intraband transition properties in InAs/GaAs quantum dot superlattice solar cells. <i>Applied Physics Express</i> , 2019 , 12, 125008	2.4	2
39	Increasing conversion efficiency of two-step photon up-conversion solar cell with a voltage booster hetero-interface. <i>Scientific Reports</i> , 2018 , 8, 872	4.9	8
38	Hot-carrier generation in a solar cell containing InAs/GaAs quantum-dot superlattices as a light absorber. <i>Applied Physics Express</i> , 2018 , 11, 082303	2.4	3
37	Assessing the Nature of the Distribution of Localised States in Bulk GaAsBi. <i>Scientific Reports</i> , 2018 , 8, 6457	4.9	24
36	Two-step photocurrent generation enhanced by miniband formation in InAs/GaAs quantum dot superlattice intermediate-band solar cells. <i>Applied Physics Letters</i> , 2017 , 110, 193104	3.4	7
35	Fundamental Device Characteristics of Hot Carrier Solar Cell Using InAs/GaAs Quantum Dot Superlattices.. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2017 , 66, 629-633	0.1	
34	Efficient two-step photocarrier generation in bias-controlled InAs/GaAs quantum dot superlattice intermediate-band solar cells. <i>Scientific Reports</i> , 2017 , 7, 5865	4.9	14
33	Spatially resolved electronic structure of an isovalent nitrogen center in GaAs. <i>Physical Review B</i> , 2017 , 96,	3.3	6

32	Nanosecond-scale hot-carrier cooling dynamics in one-dimensional quantum dot superlattices. <i>Physical Review B</i> , 2016 , 93,	3.3	16
31	Polarization characteristics of electroluminescence and net modal gain in highly stacked InAs/GaAs quantum-dot laser devices. <i>Journal of Applied Physics</i> , 2016 , 120, 134313	2.5	3
30	Effects of rapid thermal annealing on two-dimensional delocalized electronic states of the epitaxial N doped layer in GaAs. <i>Applied Physics Letters</i> , 2016 , 108, 111905	3.4	4
29	Photocurrent transport dynamics in InAs/GaAs quantum dot superlattice solar cells using time-of-flight spectroscopy. <i>Physical Review B</i> , 2016 , 94,	3.3	6
28	Thermal annealing effects on ultra-violet luminescence properties of Gd doped AlN. <i>Journal of Applied Physics</i> , 2015 , 117, 163105	2.5	8
27	Two-step photon absorption in InAs/GaAs quantum-dot superlattice solar cells. <i>Physical Review B</i> , 2015 , 91,	3.3	29
26	Analysis of Optical Waveguide Mode in Closely-Stacked InAs/GaAs Quantum Dot Semiconductor Optical Amplifiers. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2015 , 64, 685-689	0.1	
25	Epitaxial two-dimensional nitrogen atomic sheet in GaAs. <i>Applied Physics Letters</i> , 2014 , 104, 041907	3.4	14
24	Polarization-insensitive optical gain characteristics of highly stacked InAs/GaAs quantum dots. <i>Journal of Applied Physics</i> , 2014 , 115, 233512	2.5	14
23	Resonant indirect excitation of Gd ³⁺ in AlN thin films. <i>Journal of Applied Physics</i> , 2014 , 115, 173508	2.5	1
22	Effect of internal electric field on InAs/GaAs quantum dot solar cells. <i>Journal of Applied Physics</i> , 2014 , 115, 083510	2.5	27
21	Hot-carrier solar cells using low-dimensional quantum structures. <i>Applied Physics Letters</i> , 2014 , 105, 171904	3.4	14
20	Polarization controlled emission from closely stacked InAs/GaAs quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1492-1495		1
19	One-dimensional miniband formation in closely stacked InAs/GaAs quantum dots. <i>Physical Review B</i> , 2013 , 87,	3.3	40
18	Control of stacking direction and optical anisotropy in InAs/GaAs quantum dots by In flux. <i>Journal of Applied Physics</i> , 2013 , 114, 033517	2.5	5
17	Intraband carrier dynamics in InAs/GaAs quantum dots stimulated by bound-to-continuum excitation. <i>Journal of Applied Physics</i> , 2013 , 113, 223511	2.5	22
16	High-resolution optical coherence tomography using broadband light source with strain-controlled InAs/GaAs quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 2473-2476		1
15	Carrier dynamics of the intermediate state in InAs/GaAs quantum dots coupled in a photonic cavity under two-photon excitation. <i>Physical Review B</i> , 2012 , 86,	3.3	29

14	Near-field photoluminescence spectroscopy of CdTe/Cd _{0.75} Mn _{0.25} Te tilted superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 262-265		
13	Extremely uniform bound exciton states in nitrogen doped GaAs studied by photoluminescence spectroscopy in external magnetic fields. <i>Journal of Applied Physics</i> , 2011 , 110, 083522	2.5	9
12	Intermediate band photovoltaics based on interband/intraband transitions using In _{0.53} Ga _{0.47} As/InP superlattice. <i>Progress in Photovoltaics: Research and Applications</i> , 2011 , 21, n/a-n/a	6.8	7
11	Bound biexciton luminescence in nitrogen doped GaAs. <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 464-467	1.3	7
10	Interaction between conduction-band edge and nitrogen-related localized levels in nitrogen doped GaAs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 365-367		1
9	Experimental and atomistic theoretical study of degree of polarization from multilayer InAs/GaAs quantum dot stacks. <i>Physical Review B</i> , 2011 , 84,	3.3	41
8	Multidirectional Observation of Photoluminescence Polarization Anisotropy in Closely Stacked InAs/GaAs Quantum Dots. <i>Applied Physics Express</i> , 2011 , 4, 062001	2.4	36
7	Statistical fluctuation of magnetization in Mn-composition modulated Cd _{1-x} MnxTe quantum wires. <i>Journal of Applied Physics</i> , 2010 , 107, 043521	2.5	1
6	Anisotropic linear-polarization luminescence in CdTe/CdMnTe quantum wires. <i>Journal of Luminescence</i> , 2009 , 129, 1448-1453	3.8	
5	Anisotropic magneto-optical effects in CdTe/Cd _{0.75} Mn _{0.25} Te quantum wire structures. <i>Physical Review B</i> , 2008 , 78,	3.3	3
4	Fine structure splitting of isoelectronic bound excitons in nitrogen-doped GaAs. <i>Physical Review B</i> , 2008 , 77,	3.3	20
3	Anisotropic magneto-optical effects in one-dimensional diluted magnetic semiconductors. <i>Physical Review B</i> , 2006 , 74,	3.3	16
2	Valence-band mixing induced by sp-d exchange interaction in CdMnTe quantum wires. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 667-670		1
1	Anisotropic exchange interaction caused by hole-spin reorientation in (CdTe) _{0.5} (Cd _{0.75} Mn _{0.25} Te) _{0.5} tilted superlattices grown on Cd _{0.74} Mg _{0.26} Te(001) vicinal surface. <i>Journal of Crystal Growth</i> , 2005 , 275, e2221-e2224	1.6	3